

NDC7003P

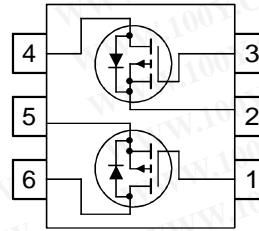
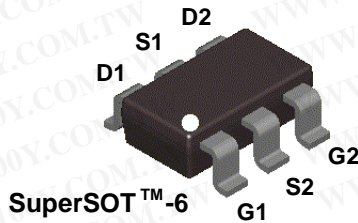
Dual P-Channel PowerTrench® MOSFET

General Description

These dual P-Channel Enhancement Mode Power Field Effect Transistors are produced using Fairchild's proprietary Trench Technology. This very high density process has been designed to minimize on-state resistance, provide rugged and reliable performance and fast switching. This product is particularly suited to low voltage applications requiring a low current high side switch.

Features

- -0.34A, -60 V. $R_{DS(ON)} = 5 \Omega @ V_{GS} = -10 V$
 $R_{DS(ON)} = 7 \Omega @ V_{GS} = -4.5 V$
- Low gate charge
- Fast switching speed
- High performance trench technology for low $R_{DS(ON)}$
- SuperSOT™ -6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick)



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
V_{DSS}	Drain-Source Voltage	-60	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous (Note 1a)	-0.34	A
	– Pulsed	-1	
P_D	Power Dissipation for Single Operation (Note 1a)	0.96	W
	(Note 1b)	0.9	
	(Note 1c)	0.7	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	130	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	60	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.03P	NDC7003P	7"	8mm	3000 units

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		-57		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
I_{GSS}	Gate-Body Leakage,	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			± 100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-1	-1.9	-3.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		3.2		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -0.34\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -0.25\text{ A}$ $V_{GS} = -10\text{ V}, I_D = -0.34\text{ A}, T_J = 125^\circ\text{C}$		1.2 1.5 1.9	5 7.5 10	Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = -10\text{ V}, V_{DS} = -10\text{ V}$	-1			A
g_{FS}	Forward Transconductance	$V_{DS} = -10\text{ V}, I_D = -0.34\text{ A}$		700		mS

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		66		pF
C_{oss}	Output Capacitance			13		pF
C_{rss}	Reverse Transfer Capacitance			6		pF
R_G	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$		11.2		Ω

Switching Characteristics (Note 2)

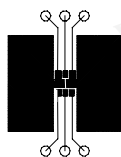
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -25\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -10\text{ V}, R_{GEN} = 6\ \Omega$		3.2	6.4	ns
t_r	Turn-On Rise Time			10	20	ns
$t_{d(off)}$	Turn-Off Delay Time			8	16	ns
t_f	Turn-Off Fall Time			1	2	ns
Q_g	Total Gate Charge	$V_{DS} = -25\text{ V}, I_D = -0.34\text{ A},$ $V_{GS} = -10\text{ V}$		1.6	2.2	nC
Q_{gs}	Gate-Source Charge			0.3		nC
Q_{gd}	Gate-Drain Charge			0.3		nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current			-0.34		A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -0.34\text{ A}$ (Note 2)		-0.8	-1.4	V

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



- a) 130°C/W when mounted on a 0.125 in^2 pad of 2 oz. copper.



- b) 140°C/W when mounted on a $.005\text{ in}^2$ pad of 2 oz copper



- c) 180°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < $300\ \mu\text{s}$, Duty Cycle < 2.0%

Typical Characteristics

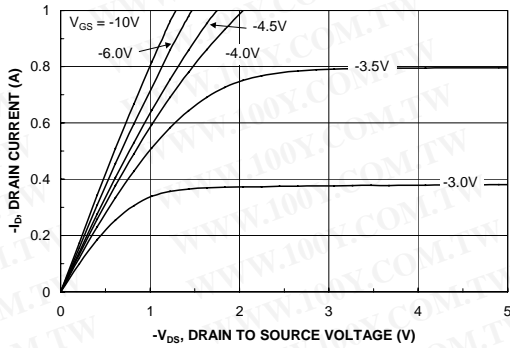


Figure 1. On-Region Characteristics.

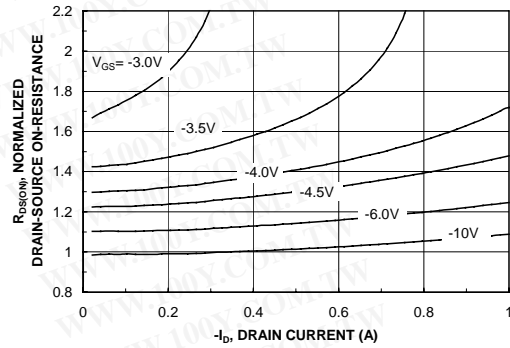


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

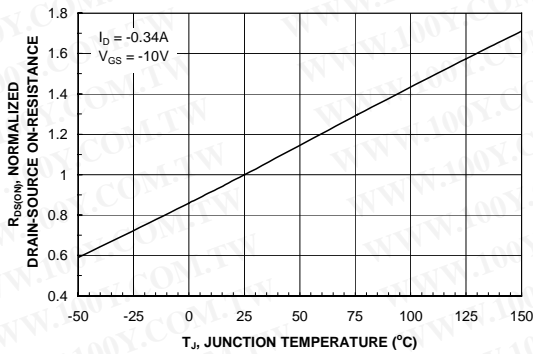


Figure 3. On-Resistance Variation with Temperature.

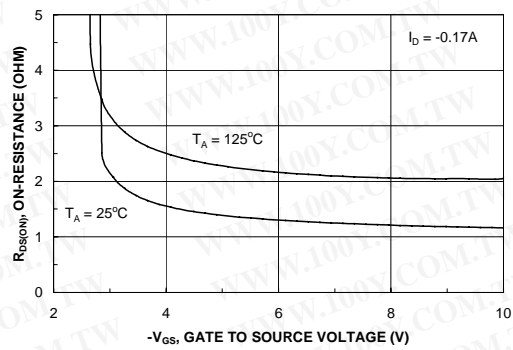


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

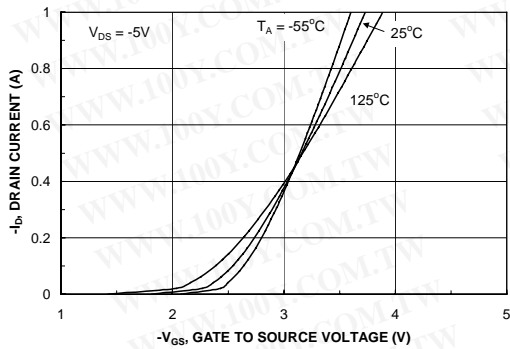


Figure 5. Transfer Characteristics.

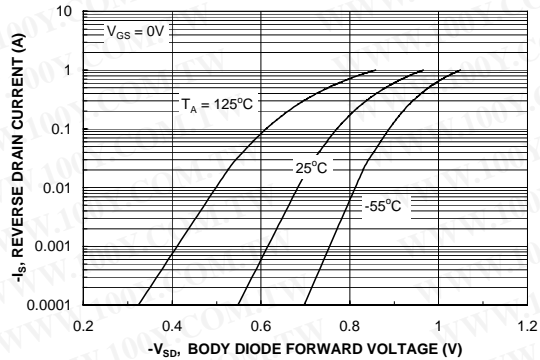


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

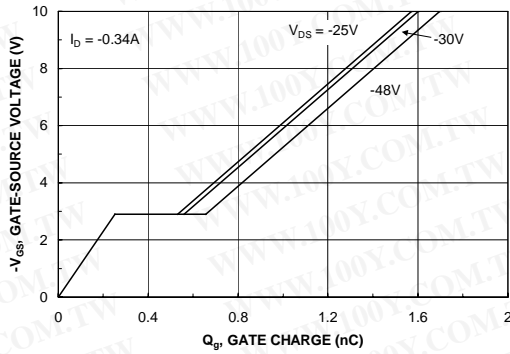


Figure 7. Gate Charge Characteristics.

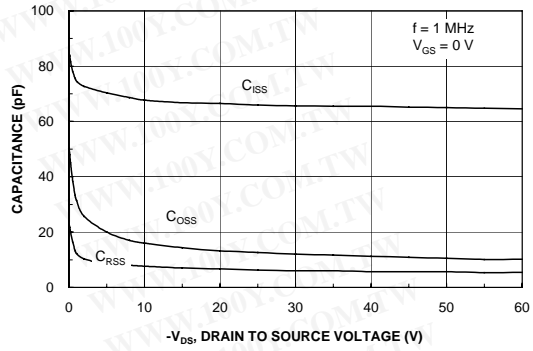


Figure 8. Capacitance Characteristics.

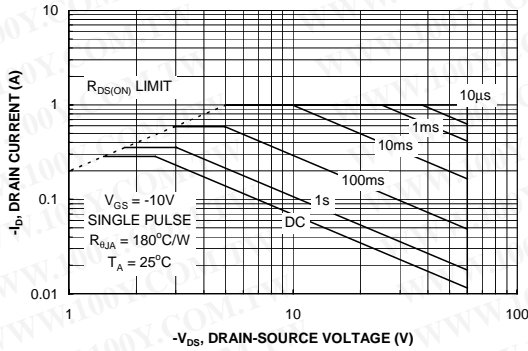


Figure 9. Maximum Safe Operating Area.

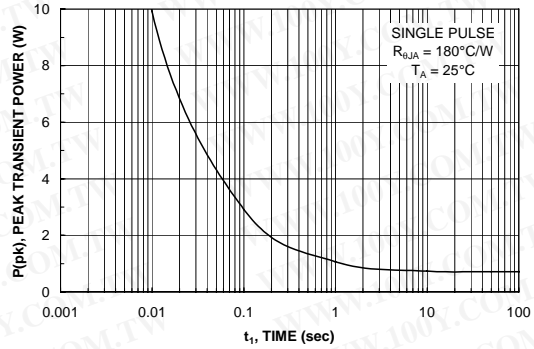


Figure 10. Single Pulse Maximum Power Dissipation.

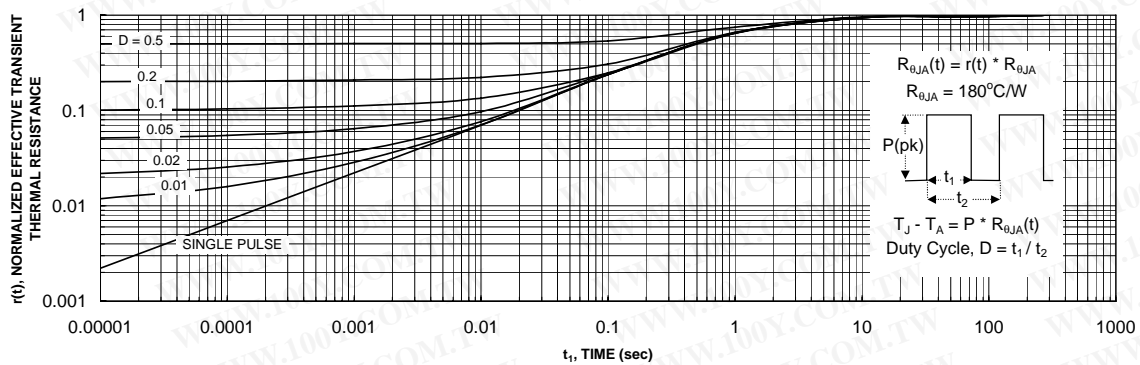


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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DOMETM	HiSeC™	Power247™	SuperSOT™-3	
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E ² CMOS™	ISOPLANAR™	QFET™	SuperSOT™-8	
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